

Transistors

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=50V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_B=5mA/0.25mA$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE}=5V, I_C=1mA$
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=10mA, I_E=-5mA, f=100MHz$ *
Input resistance	R_1	3.29	4.7	6.11	k Ω	—

* Transition frequency of the transistor

●Packaging specifications

Type	Package	Taping		
	Code	T2R	TR	T108
	Basic ordering unit (pieces)	8000	3000	3000
EMD6	○	—	—	—
UMD6N	—	○	—	—
IMD6A	—	—	—	○

●Electrical characteristic curves

DTr1 (NPN)

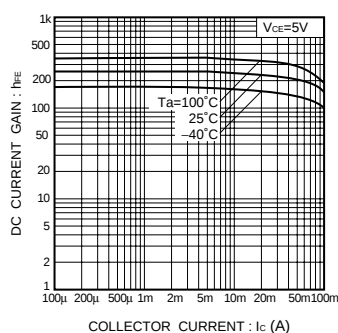


Fig.1 DC current gain vs. collector current

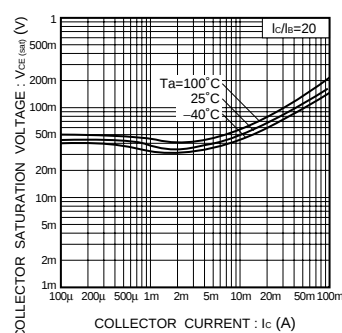


Fig.2 Collector-emitter saturation voltage vs. collector current

DTr2 (PNP)

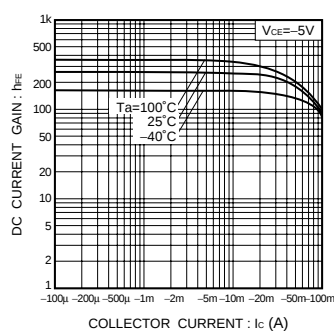


Fig.3 DC current gain vs. collector current

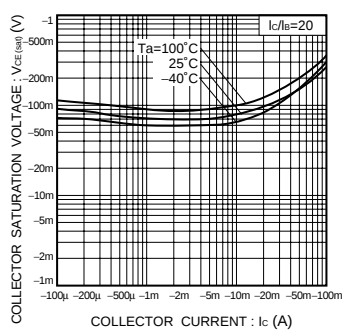


Fig.4 Collector-emitter saturation voltage vs. collector current